L Number	Hits	Search Text	DB	Time stamp
1	90355	(anneal\$3 heat\$3 bak\$3 thermal thermally) near15 (hydrogen	USPAT;	2002/09/21 17:56
·		"H.sub.2" HCI)	US-PGPUB;	
		,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
8	9612	((anneal\$3 heat\$3 bak\$3 thermal thermally) near15	USPAT;	2002/09/21 17:56
	55.2	(hydrogen "H.sub.2" HCI)) near15 (silicon semiconductor	US-PGPUB;	
		substrate SOI wafer)	EPO: JPO:	
		,	DERWENT:	
			IBM TDB	
15	211	(((anneal\$3 heat\$3 bak\$3 thermal thermally) near15	USPAT:	2002/09/21 17:58
	211	(hydrogen "H.sub.2" HCl)) near15 (silicon semiconductor	US-PGPUB:	
		substrate SOI wafer)) same (atm or (atmospheric adj	EPO: JPO:	
		pressure) or (("750" "760") adj torr))	DERWENT:	
		pressure/ or ((100 100) aug (011))	IBM TDB	